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#5/Amend  
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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jiunn-Ren Hwang      Examiner: Ruggles, John S

5                                  Anseime Chen

                                I-Hsiung Huang

Filing Date: 05/10/2001      Art Unit: 1756

Serial No.: 09/851,580      Docket No.: NAUP0292USA

10 Title: METHOD OF FORMING STORAGE NODES IN A DRAM

To: The Commissioner of Patents and Trademarks  
Washington, D.C. 20231

15 Subject: Reply to the Office Action dated 12/18/2002

Dear Sir:

**AMENDMENT**

20 In response to the Office Action noted above, please amend the above-identified application as follows:

**In the Abstract:**

On page 1, please replace the whole paragraph beginning on line 4 as following:

25 A dynamic random access memory (DRAM) is formed on a semiconductor wafer including a substrate, a thin film layer positioned on the substrate, and a photoresist layer positioned on the thin film layer. A first exposure process is performed to form first exposure regions including a plurality of lines parallel to each other and covering each storage node. A second exposure process is performed to form second exposure regions cutting the plurality of lines of the first exposure regions.

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